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secondary electron emission

three-step process:

- production of SEs at a depth z
- transport of the SE toward the surface
- emission of SE across the surface barrier



universal curve

the material parameters influencing SEY are: penetration depth of the primary electrons, stopping power, escape depth of the secondary electrons, work function - Z number

Spread in the SEY data



Lin et al. SIA 2005, 37 895



the effective SEY of the metal is strongly modified by the surface contamination

X-ray photoelectron spectroscopy



XPS spectroscopy of technical samples



SEY of technical samples



high SEY medium SEY low SEY

SEY of technical samples



SEY of technical samples



dissociation of "environmental" molecules \rightarrow reactions, film growth



SEY decreases also outside the beam spot



the beam spot but also the surrounding area is modified

in the beam spot the quantity of surface C increases \rightarrow graphitic film growth



e⁻ beam induced surface reactions



the contribution of all electron-induced surface reactions reduces δ_{max} from 2.2 to 1.1



R. Cimino et al. submitted to PRL



Stainless steel samples from RICH@BNL

E=500 eV





D. Grosso et al. submitted to PR-ST





72.5 eV Al metallic

73.4 eV AI bonded to chemisorbed O

73.9 eV tetrahedral Al₂O₃

75.1 eV octahedral Al₂O₃

the minimal partial pressure of H_2O contained in the residual gas is sufficient to hinder the achievement of a stable, clean Al surface.

After prolonged ion bombardment there are still AI atoms bonded to O even in a AI₂O₃ phases

D. Grosso et al. submitted to PR-ST





dissociation of residual gas molecules as H_2O and CO induced at the metal surface by the e⁻ beam determines a rapid oxidation of the irradiated area, as well as, although to a lesser extent, of the surrounding region





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73.4 eV AI bonded to chemisorbed O
73.9 eV tetrahedral Al₂O₃
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D. Grosso et al. submitted to PR-ST



the SEY variation follows the oxygen content of the AI surface

D. Grosso et al. submitted to PR-ST

e⁻ beam induced surface reactions



SEY is determined by the rates of AI oxidation and reduction



C films on polycrystalline Cu

a-C films magnetron sputtering @ RT $p(Ar)= 10^{-2}$ mbar $\Delta t = 2min$

C film thickness 2-3 nm

C films on polycristalline Cu

the graphitization of the C films corresponds to a lower SEY

Conclusions

The SEY of technical samples is strongly affected by the chemical composition of the surface as the presence and the nature of contaminating adsorbates can heavily modify the effective δ_{max} values. This determines the high variation of the experimental values.

For Cu samples electron conditioning at 500 eV reduces the SEY and lowers δ_{max} from 2.2 to 1.1. Both direct beam and secondary electrons have a role in the chemical reactions which decrease the SEY.

Similar results were found for stainless steel samples.

On the contrary for AI samples electron conditioning at 500 eV does not succeed in lowering δ_{max} below 1.8 (1.5). In this case the composition of the residual gas in the UHV chamber is extremely important limiting the e⁻ beam induced oxidation.

For ultrathin C films deposited by magnetron sputtering on copper δ_{max} depends on the sp³/sp² ratio.

The knowledge of the chemical state of a "technical" surface can elucidate the origin of the measured SEY curves and in general provide profitable information for the e-cloud mitigation.

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